Ordering number : ENN7081

N-Channel Silicon MOSFET

2SK2625LS

Ultrahigh-Speed Switching Applications

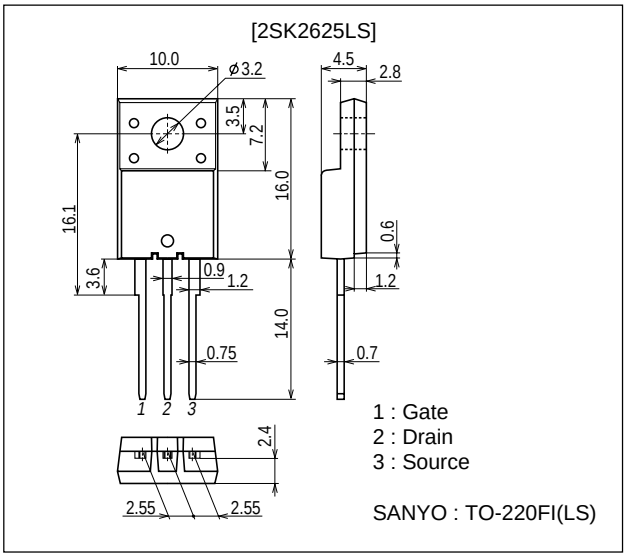
Features

- Low ON-resistance.
- Low Qg.

Package Dimensions

unit : mm

2078C



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		600	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_D		4	A
Drain Current (Pulse)	I_{DP}		16	A
Allowable Power Dissipation	P_D		2.0	W
		Tc=25°C	30	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	600			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V, V_{GS}=0			1.0	mA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0			±100	nA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	3.5		5.5	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=2.5A	1.5	3.0		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)$	I_D=2.5A, V_{GS}=15V		1.5	2.0	Ω

Marking : K2625

Continued on next page.

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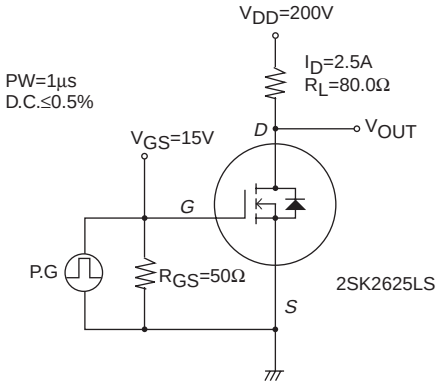
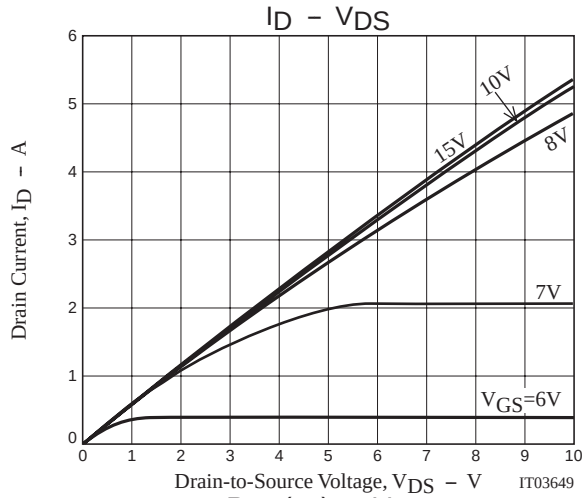
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

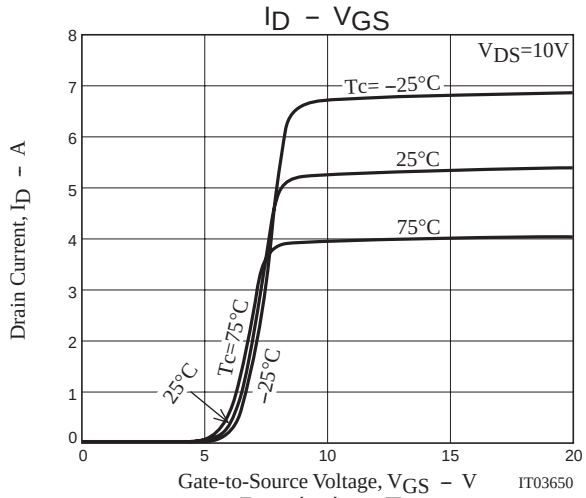
Continued from preceding page.

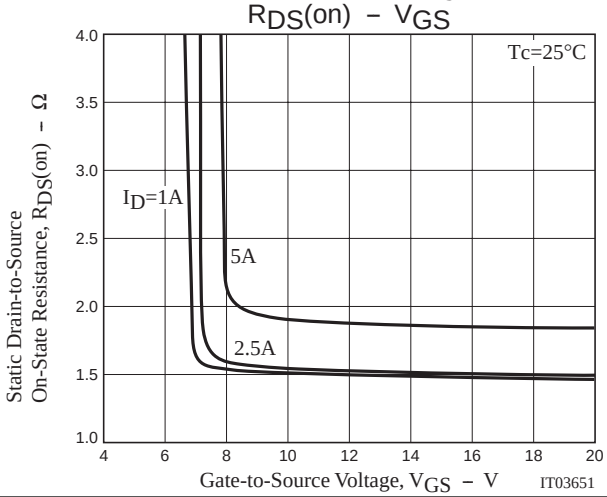
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		700		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		220		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		110		pF
Total Gate Charge	Qg	V_{DS}=200V, I_D=5A, V_{GS}=10V		20		nC
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		20		ns
Rise Time	t_r	See specified Test Circuit.		20		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.		50		ns
Fall Time	t_f	See specified Test Circuit.		25		ns
Diode Forward Voltage	V_{SD}	I_S=5A, V_{GS}=0		0.88	1.2	V

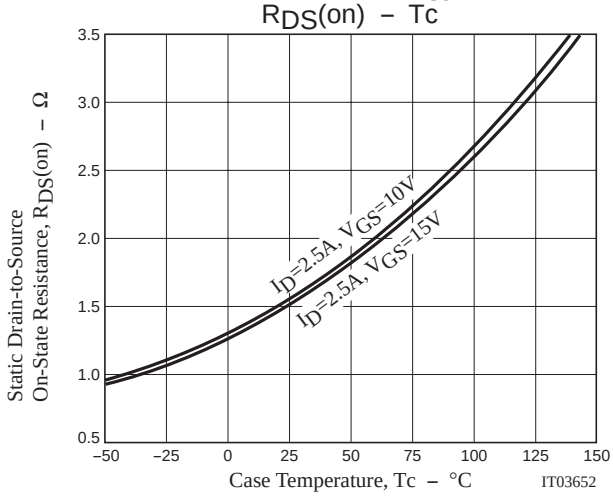
Switching Time Test Circuit

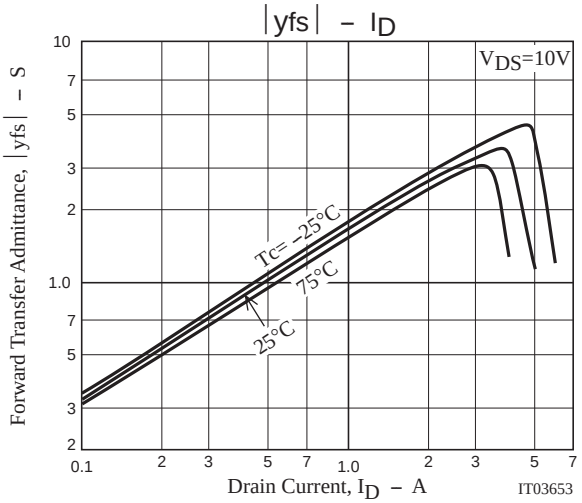


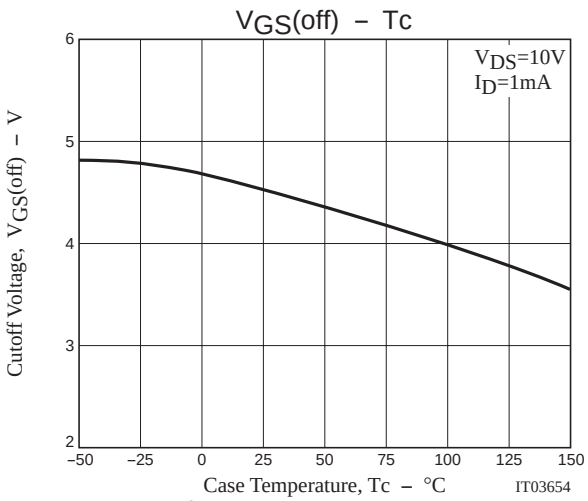


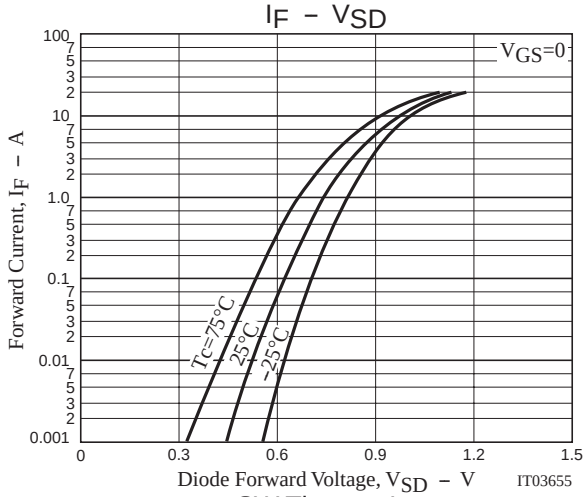


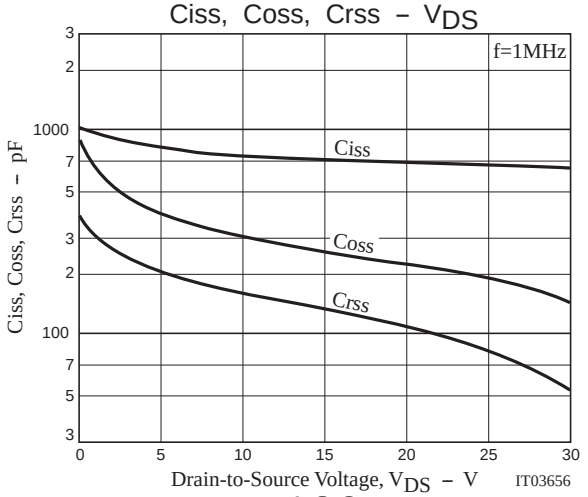


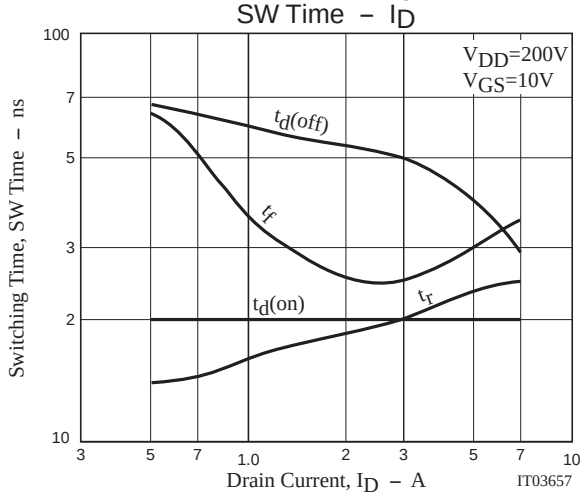


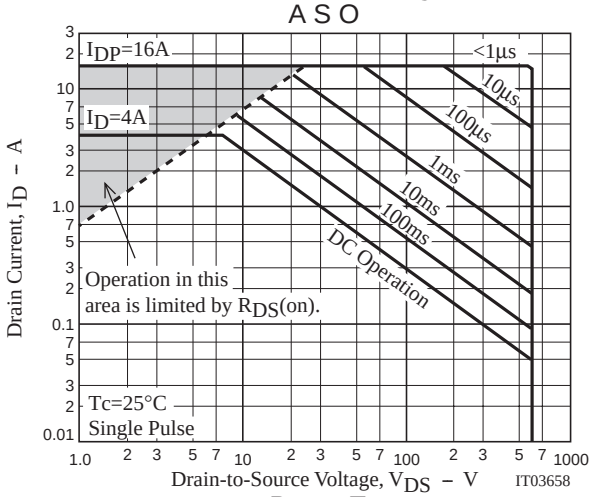

|yfs| – ID
VDS=10V
Tc=–25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT03653

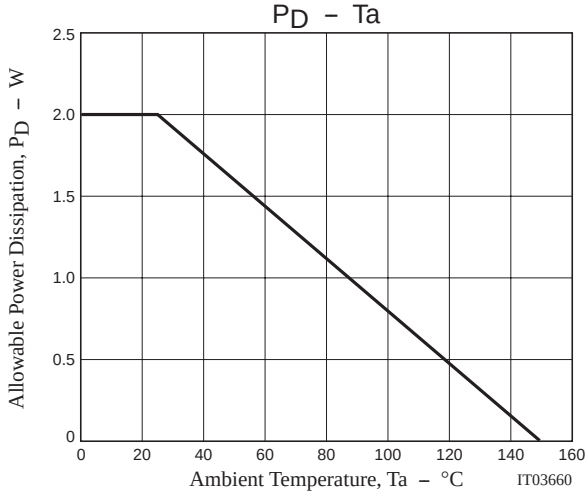

VGS(off) – Tc
VDS=10V
ID=1mA
Cutoff Voltage, VGS(off) – V
Case Temperature, Tc – °C
IT03654

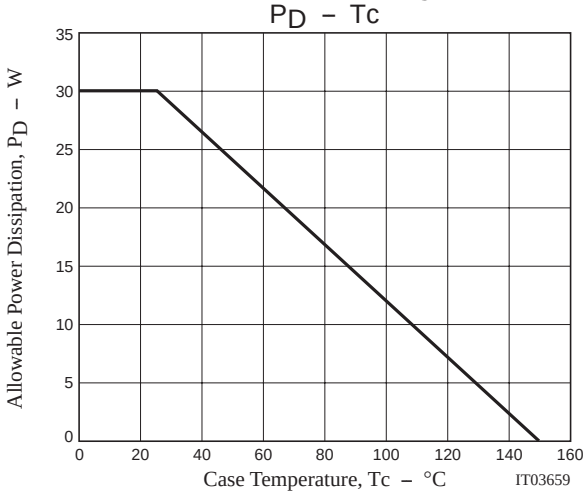

IF – VSD
VGS=0
Tc=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT03655


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT03656


SW Time – ID
VDD=200V
VGS=10V
td(off)
tf
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT03657


A S O
IDP=16A
ID=4A
<1µs
10µs
100µs
1ms
10ms
100ms
DC Operation
Operation in this
area is limited by RDS(on).
Tc=25°C
Single Pulse
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT03658


PD – Ta
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT03660


PD – Tc
Allowable Power Dissipation, PD – W
Case Temperature, Tc – °C
IT03659